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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	49
Number of Gates	15000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn015-qng68i

3 – Global Resources in Low Power Flash Devices

Introduction

IGLOO, Fusion, and ProASIC3 FPGA devices offer a powerful, low-delay VersaNet global network scheme and have extensive support for multiple clock domains. In addition to the Clock Conditioning Circuits (CCCs) and phase-locked loops (PLLs), there is a comprehensive global clock distribution network called a VersaNet global network. Each logical element (VersaTile) input and output port has access to these global networks. The VersaNet global networks can be used to distribute low-skew clock signals or high-fanout nets. In addition, these highly segmented VersaNet global networks contain spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside their region. This allows users the flexibility to create low-skew local clock networks using spines. This document describes VersaNet global networks and discusses how to assign signals to these global networks and spines in a design flow. Details concerning low power flash device PLLs are described in the "Clock Conditioning Circuits in Low Power Flash Devices and Mixed Signal FPGAs" section on page 61. This chapter describes the low power flash devices' global architecture and uses of these global networks in designs.

Global Architecture

Low power flash devices offer powerful and flexible control of circuit timing through the use of global circuitry. Each chip has up to six CCCs, some with PLLs.

- In IGLOOe, ProASIC3EL, and ProASIC3E devices, all CCCs have PLLs—hence, 6 PLLs per device (except the PQ208 package, which has only 2 PLLs).
- In IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3, and ProASIC3L devices, the west CCC contains a PLL core (except in 10 k through 30 k devices).
- In Fusion devices, the west CCC also contains a PLL core. In the two larger devices (AFS600 and AFS1500), the west and east CCCs each contain a PLL.

Refer to Table 4-6 on page 84 for details. Each PLL includes delay lines, a phase shifter (0°, 90°, 180°, 270°), and clock multipliers/dividers. Each CCC has all the circuitry needed for the selection and interconnection of inputs to the VersaNet global network. The east and west CCCs each have access to three chip global lines on each side of the chip (six chip global lines total). The CCCs at the four corners each have access to three quadrant global lines in each quadrant of the chip (except in 10 k through 30 k gate devices).

The nano 10 k, 15 k, and 20 k devices support four VersaNet global resources, and 30 k devices support six global resources. The 10 k through 30 k devices have simplified CCCs called CCC-GLs.

The flexible use of the VersaNet global network allows the designer to address several design requirements. User applications that are clock-resource-intensive can easily route external or gated internal clocks using VersaNet global routing networks. Designers can also drastically reduce delay penalties and minimize resource usage by mapping critical, high-fanout nets to the VersaNet global network.

Note: Microsemi recommends that you choose the appropriate global pin and use the appropriate global resource so you can realize these benefits.

The following sections give an overview of the VersaNet global network, the structure of the global network, access point for the global networks, and the clock aggregation feature that enables a design to have very low clock skew using spines.

Step 1

Run Synthesis with default options. The Synplicity log shows the following device utilization:

Cell usage:

	cell count	area	count*area
DFN1E1C1	1536	2.0	3072.0
BUFF	278	1.0	278.0
INBUF	10	0.0	0.0
VCC	9	0.0	0.0
GND	9	0.0	0.0
OUTBUF	6	0.0	0.0
CLKBUF	3	0.0	0.0
PLL	2	0.0	0.0
TOTAL	1853		3350.0

Step 2

Run Compile with the **Promote regular nets whose fanout is greater than** option selected in Designer; you will see the following in the Compile report:

Device utilization report:

```
=====
CORE                Used:   1536  Total:  13824  (11.11%)
IO (W/ clocks)      Used:    19   Total:   147   (12.93%)
Differential IO      Used:     0   Total:    65   (0.00%)
GLOBAL              Used:     8   Total:    18   (44.44%)
PLL                 Used:     2   Total:     2   (100.00%)
RAM/FIFO            Used:     0   Total:    24   (0.00%)
FlashROM            Used:     0   Total:     1   (0.00%)
=====
```

The following nets have been assigned to a global resource:

Fanout	Type	Name
1536	INT_NET	Net : EN_ALL_c Driver: EN_ALL_pad_CLKINT Source: AUTO PROMOTED
1536	SET/RESET_NET	Net : ACLR_c Driver: ACLR_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK1_c Driver: QCLK1_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK2_c Driver: QCLK2_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : QCLK3_c Driver: QCLK3_pad_CLKINT Source: AUTO PROMOTED
256	CLK_NET	Net : \$1N14 Driver: \$1I5/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N12 Driver: \$1I6/Core Source: ESSENTIAL
256	CLK_NET	Net : \$1N10 Driver: \$1I6/Core Source: ESSENTIAL

Designer will promote five more signals to global due to high fanout. There are eight signals assigned to global networks.

CCC Support in Microsemi's Flash Devices

The flash FPGAs listed in Table 4-1 support the CCC feature and the functions described in this document.

Table 4-1 • Flash-Based FPGAs

Series	Family*	Description
IGLOO	IGLOO	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLOOe	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
	IGLOO nano	The industry's lowest-power, smallest-size solution
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM® Cortex™-M1 soft processors, and flash memory into a monolithic device

Note: *The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 4-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

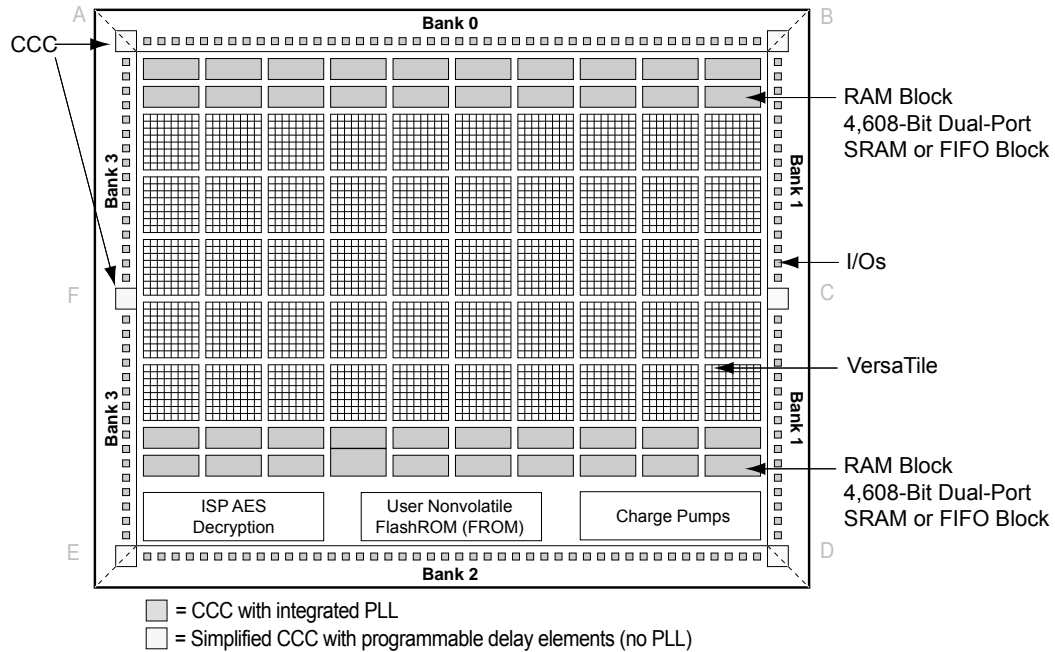
ProASIC3 Terminology

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 4-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.

IGLOO and ProASIC3 CCC Locations

In all IGLOO and ProASIC3 devices (except 10 k through 30 k gate devices, which do not contain PLLs), six CCCs are located in the same positions as the IGLOOe and ProASIC3E CCCs. Only one of the CCCs has an integrated PLL and is located in the middle of the west (middle left) side of the device. The other five CCCs are simplified CCCs and are located in the four corners and the middle of the east side of the device (Figure 4-14).



**Figure 4-14 • CCC Locations in IGLOO and ProASIC3 Family Devices
(except 10 k through 30 k gate devices)**

Note: The number and architecture of the banks are different for some devices.

10 k through 30 k gate devices do not support PLL features. In these devices, there are two CCC-GLs at the lower corners (one at the lower right, and one at the lower left). These CCC-GLs do not have programmable delays.

Table 4-13 • 2-Bit Feedback MUX

FBSEL<1:0> State	MUX Input Selected
0	Ground. Used for power-down mode in power-down logic block.
1	PLL VCO 0° phase shift
2	PLL delayed VCO 0° phase shift
3	N/A

Table 4-14 • Programmable Delay Selection for Feedback Delay and Secondary Core Output Delays

FBDLY<4:0>; DLYYB<4:0>; DLYYC<4:0> State	Delay Value
0	Typical delay = 600 ps
1	Typical delay = 760 ps
2	Typical delay = 920 ps
⋮	⋮
31	Typical delay = 5.56 ns

Table 4-15 • Programmable Delay Selection for Global Clock Output Delays

DLYGLA<4:0>; DLYGLB<4:0>; DLYGLC<4:0> State	Delay Value
0	Typical delay = 225 ps
1	Typical delay = 760 ps
2	Typical delay = 920 ps
⋮	⋮
31	Typical delay = 5.56 ns

Table 4-16 • Fusion Dynamic CCC Clock Source Selection

RXASEL	DYNASEL	Source of CLKA
1	0	RC Oscillator
1	1	Crystal Oscillator
RXBSEL	DYNBSEL	Source of CLKB
1	0	RC Oscillator
1	1	Crystal Oscillator
RXCSEL	DYNCSEL	Source of CLKC
1	0	RC Oscillator
1	1	Crystal Oscillator

Table 4-17 • Fusion Dynamic CCC NGMUX Configuration

GLMUXCFG<1:0>	NGMUX Select Signal	Supported Input Clocks to NGMUX
00	0	GLA
	1	GLC
01	0	GLA
	1	GLINT
10	0	GLC
	1	GLINT

Table 6-8 and Table 6-9 show the maximum potential width and depth configuration for each device. Note that 15 k and 30 k gate devices do not support RAM or FIFO.

Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device

Device		RAM Blocks	Maximum Potential Width ¹		Maximum Potential Depth ²	
IGLOO IGLOO nano IGLOO PLUS	ProASIC3 ProASIC3 nano ProASIC3L		Depth	Width	Depth	Width
AGL060 AGLN060 AGLP060	A3P060 A3PN060	4	256	72 (4×18)	16,384 (4,096×4)	1
AGL125 AGLN125 AGLP125	A3P125 A3PN125	8	256	144 (8×18)	32,768 (4,096×8)	1
AGL250 AGLN250	A3P250/L A3PN250	8	256	144 (8×18)	32,768 (4,096×8)	1
AGL400	A3P400	12	256	216 (12×18)	49,152 (4,096×12)	1
AGL600	A3P600/L	24	256	432 (24×18)	98,304 (4,096×24)	1
AGL1000	A3P1000/L	32	256	576 (32×18)	131,072 (4,096×32)	1
AGLE600	A3PE600	24	256	432 (24×18)	98,304 (4,096×24)	1
	A3PE1500	60	256	1,080 (60×18)	245,760 (4,096×60)	1
AGLE3000	A3PE3000/L	112	256	2,016 (112×18)	458,752 (4,096×112)	1

Notes:

1. Maximum potential width uses the two-port configuration.
2. Maximum potential depth uses the dual-port configuration.

Table 6-9 • Memory Availability per Fusion Device

Device	RAM Blocks	Maximum Potential Width ¹		Maximum Potential Depth ²	
		Depth	Width	Depth	Width
AFS090	6	256	108 (6×18)	24,576 (4,096×6)	1
AFS250	8	256	144 (8×18)	32,768 (4,096×8)	1
AFS600	24	256	432 (24×18)	98,304 (4,096×24)	1
AFS1500	60	256	1,080 (60×18)	245,760 (4,096×60)	1

Notes:

1. Maximum potential width uses the two-port configuration.
2. Maximum potential depth uses the dual-port configuration.

recommended, since it reduces the complexity of the user interface block and the board-level JTAG driver.

Moreover, using an internal counter for address generation speeds up the initialization procedure, since the user only needs to import the data through the JTAG port.

The designer may use different methods to select among the multiple RAM blocks. Using counters along with demultiplexers is one approach to set the write enable signals. Basically, the number of RAM blocks needing initialization determines the most efficient approach. For example, if all the blocks are initialized with the same data, one enable signal is enough to activate the write procedure for all of them at the same time. Another alternative is to use different opcodes to initialize each memory block. For a small number of RAM blocks, using counters is an optimal choice. For example, a ring counter can be used to select from multiple RAM blocks. The clock driver of this counter needs to be controlled by the address generation process.

Once the addressing of one block is finished, a clock pulse is sent to the (ring) counter to select the next memory block.

Figure 6-9 illustrates a simple block diagram of an interface block between UJTAG and RAM blocks.

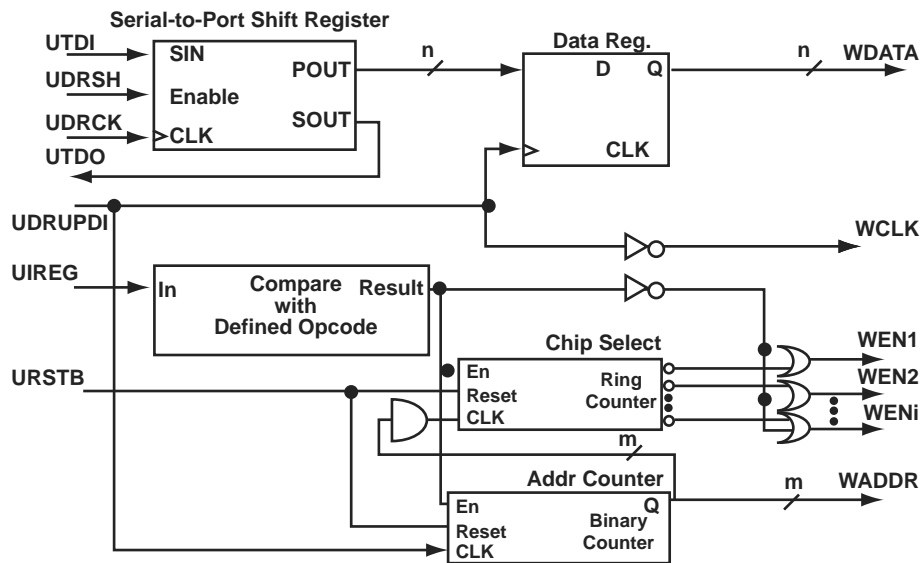


Figure 6-9 • Block Diagram of a Sample User Interface

In the circuit shown in Figure 6-9, the shift register is enabled by the UDRSH output of the UJTAG macro. The counters and chip select outputs are controlled by the value of the TAP Instruction Register. The comparison block compares the UIREG value with the "start initialization" opcode value (defined by the user). If the result is true, the counters start to generate addresses and activate the WEN inputs of appropriate RAM blocks.

The UDRUPDI output of the UJTAG macro, also shown in Figure 6-9, is used for generating the write clock (WCLK) and synchronizing the data register and address counter with WCLK. UDRUPDI is HIGH when the TAP Controller is in the Data Register Update state, which is an indication of completing the loading of one data word. Once the TAP Controller goes into the Data Register Update state, the UDRUPDI output of the UJTAG macro goes HIGH. Therefore, the pipeline register and the address counter place the proper data and address on the outputs of the interface block. Meanwhile, WCLK is defined as the inverted UDRUPDI. This will provide enough time (equal to the UDRUPDI HIGH time) for the data and address to be placed at the proper ports of the RAM block before the rising edge of WCLK. The inverter is not required if the RAM blocks are clocked at the falling edge of the write clock. An example of this is described in the "Example of RAM Initialization" section on page 150.

Table 7-10 • Hot-Swap Level 3

Description	Hot-swap while bus idle
Power Applied to Device	Yes
Bus State	Held idle (no ongoing I/O processes during insertion/removal)
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power-down
Example Application	Board bus shared with card bus is "frozen," and there is no toggling activity on the bus. It is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of nano Devices	Compliant

Table 7-11 • Hot-Swap Level 4

Description	Hot-swap on an active bus
Power Applied to Device	Yes
Bus State	Bus may have active I/O processes ongoing, but device being inserted or removed must be idle.
Card Ground Connection	Reset must be maintained for 1 ms before, during, and after insertion/removal.
Device Circuitry Connected to Bus Pins	Must remain glitch-free during power-up or power-down
Example Application	There is activity on the system bus, and it is critical that the logic states set on the bus signal not be disturbed during card insertion/removal.
Compliance of nano Devices	Compliant

For Level 3 and Level 4 compliance with the nano devices, cards with two levels of staging should have the following sequence:

- Grounds
- Powers, I/Os, and other pins

- If one of the registers has a PRE pin, all the other registers that are candidates for combining in the I/O must have a PRE pin.
 - If one of the registers has neither a CLR nor a PRE pin, all the other registers that are candidates for combining must have neither a CLR nor a PRE pin.
 - If the clear or preset pins are present, they must have the same polarity.
 - If the clear or preset pins are present, they must be driven by the same signal (net).
3. For single-tile devices (10 k, 15 k, and 20 k): Registers connected to an I/O on the Output and Output Enable pins must have the same clock function (both CLR and CLK are shared among all registers):
 - Both the Output and Output Enable registers must not have an E pin (clock enable).
 4. For dual-tile devices (60 k, 125 k, and 250 k): Registers connected to an I/O on the Output and Output Enable pins must have the same clock and enable function:
 - Both the Output and Output Enable registers must have an E pin (clock enable), or none at all.
 - If the E pins are present, they must have the same polarity. The CLK pins must also have the same polarity.

In some cases, the user may want registers to be combined with the input of a buffer while maintaining the output as-is. This can be achieved by using PDC commands as follows:

```
set_io <signal name> -REGISTER yes -----register will combine
set_preserve <signal name> ----register will not combine
```

Weak Pull-Up and Weak Pull-Down Resistors

nano devices support optional weak pull-up and pull-down resistors on each I/O pin. When the I/O is pulled up, it is connected to the V_{CCI} of its corresponding I/O bank. When it is pulled down, it is connected to GND. Refer to the datasheet for more information.

For low power applications and when using IGLOO nano devices, configuration of the pull-up or pull-down of the I/O can be used to set the I/O to a known state while the device is in Flash*Freeze mode. Refer to "Flash*Freeze Technology and Low Power Modes" in an applicable FPGA fabric user's guide for more information.

The Flash*Freeze (FF) pin cannot be configured with a weak pull-down or pull-up I/O attribute, as the signal needs to be driven at all times.

Output Slew Rate Control

The slew rate is the amount of time an input signal takes to get from logic LOW to logic HIGH or vice versa.

It is commonly defined as the propagation delay between 10% and 90% of the signal's voltage swing. Slew rate control is available for the output buffers of low power flash devices. The output buffer has a programmable slew rate for both HIGH-to-LOW and LOW-to-HIGH transitions.

The slew rate can be implemented by using a PDC command (Table 7-5 on page 163), setting it "High" or "Low" in the I/O Attribute Editor in Designer, or instantiating a special I/O macro. The default slew rate value is "High."

Microsemi recommends the high slew rate option to minimize the propagation delay. This high-speed option may introduce noise into the system if appropriate signal integrity measures are not adopted. Selecting a low slew rate reduces this kind of noise but adds some delays in the system. Low slew rate is recommended when bus transients are expected.

Output Drive

The output buffers of nano devices can provide multiple drive strengths to meet signal integrity requirements. The LVTTTL and LVCMOS (except 1.2 V LVCMOS) standards have selectable drive strengths.

Drive strength should also be selected according to the design requirements and noise immunity of the system.

Implementing I/Os in Microsemi Software

Microsemi Libero SoC software is integrated with design entry tools such as the SmartGen macro builder, the ViewDraw schematic entry tool, and an HDL editor. It is also integrated with the synthesis and Designer tools. In this section, all necessary steps to implement the I/Os are discussed.

Design Entry

There are three ways to implement I/Os in a design:

1. Use the SmartGen macro builder to configure I/Os by generating specific I/O library macros and then instantiating them in top-level code. This is especially useful when creating I/O bus structures.
2. Use an I/O buffer cell in a schematic design.
3. Manually instantiate specific I/O macros in the top-level code.

If technology-specific macros, such as INBUF_LVCMOS33 and OUTBUF_PCI, are used in the HDL code or schematic, the user will not be able to change the I/O standard later on in Designer. If generic I/O macros are used, such as INBUF, OUTBUF, TRIBUF, CLKBUF, and BIBUF, the user can change the I/O standard using the Designer I/O Attribute Editor tool.

Using SmartGen for I/O Configuration

The SmartGen tool in Libero SoC provides a GUI-based method of configuring the I/O attributes. The user can select certain I/O attributes while configuring the I/O macro in SmartGen. The steps to configure an I/O macro with specific I/O attributes are as follows:

1. Open Libero SoC.
2. On the left-hand side of the Catalog View, select **I/O**, as shown in Figure 8-2.

Figure 8-2 • SmartGen Catalog

Rules for the DDR I/O Function

- The fanout between an I/O pin (D or Y) and a DDR (DDR_REG or DDR_OUT) macro must be equal to one for the combining to happen on that pin.
- If a DDR_REG macro and a DDR_OUT macro are combined on the same bidirectional I/O, they must share the same clear signal.
- Registers will not be combined in an I/O in the presence of DDR combining on the same I/O.

Using the I/O Buffer Schematic Cell

Libero SoC software includes the ViewDraw schematic entry tool. Using ViewDraw, the user can insert any supported I/O buffer cell in the top-level schematic. Figure 8-5 shows a top-level schematic with different I/O buffer cells. When synthesized, the netlist will contain the same I/O macro.

Figure 8-5 • I/O Buffer Schematic Cell Usage

4. Right-click and then choose **Highlight VREF range**. All the pins covered by that VREF pin will be highlighted (Figure 8-14).
-

Figure 8-14 • VREF Range

Using PinEditor or ChipPlanner, VREF pins can also be assigned (Figure 8-15).

Figure 8-15 • Assigning VREF from PinEditor

To unassign a VREF pin:

1. Select the pin to unassign.
2. Right-click and choose **Use Pin for VREF**. The check mark next to the command disappears. The VREF pin is now a regular pin.

Resetting the pin may result in unassigning I/O cores, even if they are locked. In this case, a warning message appears so you can cancel the operation.

After you assign the VREF pins, right-click a VREF pin and choose **Highlight VREF Range** to see how many I/Os are covered by that pin. To unhighlight the range, choose **Unhighlight All** from the **Edit** menu.

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 9-1 • Flash-Based FPGAs.	206
	The "I/O Cell Architecture" section was updated with information applicable to nano devices.	207
	The output buffer (OUTBUF_SSTL3_I) input was changed to D, instead of Q, in Figure 9-1 • DDR Support in Low Power Flash Devices, Figure 9-3 • DDR Output Register (SSTL3 Class I), Figure 9-6 • DDR Output Register (SSTL3 Class I), Figure 9-7 • DDR Tristate Output Register, LOW Enable, 8 mA, Pull-Up (LVTTTL), and the output from the DDR_OUT macro was connected to the input of the TRIBUFF macro in Figure 9-7 • DDR Tristate Output Register, LOW Enable, 8 mA, Pull-Up (LVTTTL).	205, 209, 212, 213
v1.3 (October 2008)	The "Double Data Rate (DDR) Architecture" section was updated to include mention of the AFS600 and AFS1500 devices.	205
	The "DDR Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	206
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 9-1 • Flash-Based FPGAs: <ul style="list-style-type: none"> ProASIC3L was updated to include 1.5 V. The number of PLLs for ProASIC3E was changed from five to six. 	206
v1.1 (March 2008)	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	206

Programming Solutions

Details for the available programmers can be found in the programmer user's guides listed in the "Related Documents" section on page 231.

All the programmers except FlashPro4, FlashPro3, FlashPro Lite, and FlashPro require adapter modules, which are designed to support device packages. All modules are listed on the Microsemi SoC Products Group website at

http://www.microsemi.com/soc/products/hardware/program_debug/ss/modules.aspx. They are not listed in this document, since this list is updated frequently with new package options and any upgrades required to improve programming yield or support new families.

Table 10-3 • Programming Solutions

Programmer	Vendor	ISP	Single Device	Multi-Device	Availability
FlashPro4	Microsemi	Only	Yes	Yes ¹	Available
FlashPro3	Microsemi	Only	Yes	Yes ¹	Available
FlashPro Lite ²	Microsemi	Only	Yes	Yes ¹	Available
FlashPro	Microsemi	Only	Yes	Yes ¹	Discontinued
Silicon Sculptor 3	Microsemi	Yes ³	Yes	Cascade option (up to two)	Available
Silicon Sculptor II	Microsemi	Yes ³	Yes	Cascade option (up to two)	Available
Silicon Sculptor	Microsemi	Yes	Yes	Cascade option (up to four)	Discontinued
Sculptor 6X	Microsemi	No	Yes	Yes	Discontinued
BP MicroProgrammers	BP Microsystems	No	Yes	Yes	Contact BP Microsystems at www.bpmicro.com

Notes:

1. Multiple devices can be connected in the same JTAG chain for programming.
2. If FlashPro Lite is used for programming, the programmer derives all of its power from the target pc board's VDD supply. The FlashPro Lite's VPP and VPN power supplies use the target pc board's VDD as a power source. The target pc board must supply power to both the VDDP and VDD power pins of the ProASIC^{PLUS} device in addition to supplying VDD to the FlashPro Lite. The target pc board needs to provide at least 500 mA of current to the FlashPro Lite VDD connection for programming.
3. Silicon Sculptor II and Silicon Sculptor 3 can only provide ISP for ProASIC and ProASIC^{PLUS} families, not for Fusion, IGLOO, or ProASIC3 devices.

IEEE 1532 (JTAG) Interface

The supported industry-standard IEEE 1532 programming interface builds on the IEEE 1149.1 (JTAG) standard. IEEE 1532 defines the standardized process and methodology for ISP. Both silicon and software issues are addressed in IEEE 1532 to create a simplified ISP environment. Any IEEE 1532 compliant programmer can be used to program low power flash devices. Device serialization is not supported when using the IEEE1532 standard. Refer to the standard for detailed information about IEEE 1532.

Security

Unlike SRAM-based FPGAs that require loading at power-up from an external source such as a microcontroller or boot PROM, Microsemi nonvolatile devices are live at power-up, and there is no bitstream required to load the device when power is applied. The unique flash-based architecture prevents reverse engineering of the programmed code on the device, because the programmed data is stored in nonvolatile memory cells. Each nonvolatile memory cell is made up of small capacitors and any physical deconstruction of the device will disrupt stored electrical charges.

Each low power flash device has a built-in 128-bit Advanced Encryption Standard (AES) decryption core, except for the 30 k gate devices and smaller. Any FPGA core or FlashROM content loaded into the device can optionally be sent as encrypted bitstream and decrypted as it is loaded. This is particularly suitable for applications where device updates must be transmitted over an unsecured network such as the Internet. The embedded AES decryption core can prevent sensitive data from being intercepted (Figure 12-1 on page 265). A single 128-bit AES Key (32 hex characters) is used to encrypt FPGA core programming data and/or FlashROM programming data in the Microsemi tools. The low power flash devices also decrypt with a single 128-bit AES Key. In addition, low power flash devices support a Message Authentication Code (MAC) for authentication of the encrypted bitstream on-chip. This allows the encrypted bitstream to be authenticated and prevents erroneous data from being programmed into the device. The FPGA core, FlashROM, and Flash Memory Blocks (FBs), in Fusion only, can be updated independently using a programming file that is AES-encrypted (cipher text) or uses plain text.

Fine Tuning

In some applications, design constants or parameters need to be modified after programming the original design. The tuning process can be done using the UJTAG tile without reprogramming the device with new values. If the parameters or constants of a design are stored in distributed registers or embedded SRAM blocks, the new values can be shifted onto the JTAG TAP Controller pins, replacing the old values. The UJTAG tile is used as the “bridge” for data transfer between the JTAG pins and the FPGA VersaTiles or SRAM logic. Figure 16-5 shows a flow chart example for fine-tuning application steps using the UJTAG tile.

In Figure 16-5, the TMS signal sets the TAP Controller state machine to the appropriate states. The flow mainly consists of two steps: a) shifting the defined instruction and b) shifting the new data. If the target parameter is constantly used in the design, the new data can be shifted into a temporary shift register from UTDI. The UDRSH output of UJTAG can be used as a shift-enable signal, and UDRCK is the shift clock to the shift register. Once the shift process is completed and the TAP Controller state is moved to the Update_DR state, the UDRUPD output of the UJTAG can latch the new parameter value from the temporary register into a permanent location. This avoids any interruption or malfunctioning during the serial shift of the new value.

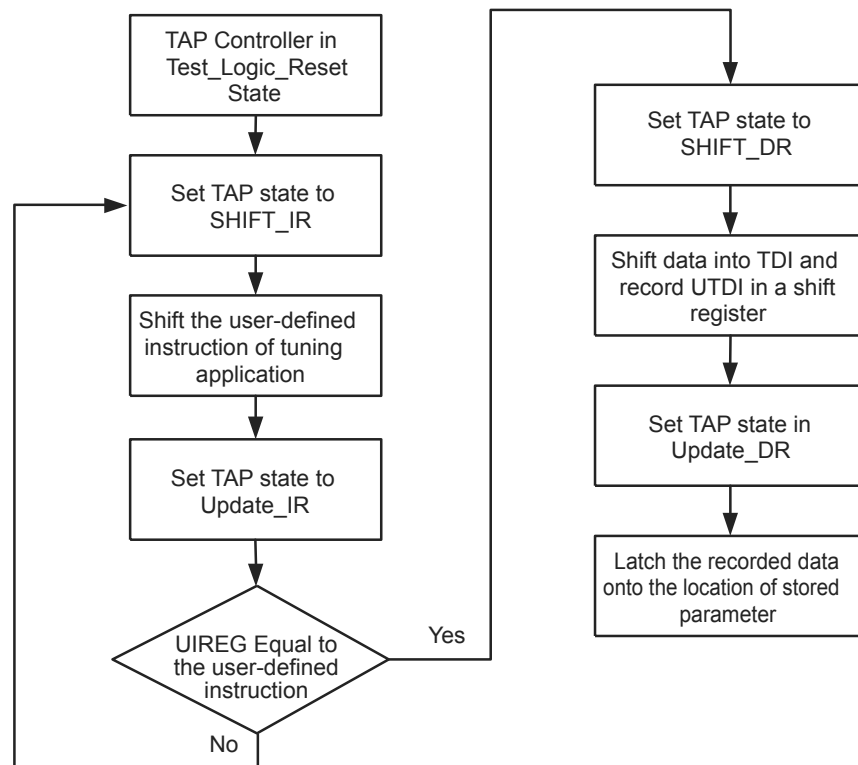


Figure 16-5 • Flow Chart Example of Fine-Tuning an Application Using UJTAG

Conclusion

Microsemi low power flash FPGAs offer many unique advantages, such as security, nonvolatility, reprogrammability, and low power—all in a single chip. In addition, Fusion, IGLOO, and ProASIC3 devices provide access to the JTAG port from core VersaTiles while the device is in normal operating mode. A wide range of available user-defined JTAG opcodes allows users to implement various types of applications, exploiting this feature of these devices. The connection between the JTAG port and core tiles is implemented through an embedded and hardwired UJTAG tile. A UJTAG tile can be instantiated in designs using the UJTAG library cell. This document presents multiple examples of UJTAG applications, such as dynamic reconfiguration, silicon test and debug, fine-tuning of the design, and RAM initialization. Each of these applications offers many useful advantages.

Related Documents

Application Notes

RAM Initialization and ROM Emulation in ProASIC^{PLUS} Devices
http://www.microsemi.com/soc/documents/APA_RAM_Initd_AN.pdf

List of Changes

The following table lists critical changes that were made in each revision of the chapter.

Date	Changes	Page
December 2011	Information on the drive strength and slew rate of TDO pins was added to the "Silicon Testing and Debugging" section (SAR 31749).	304
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 16-1 • Flash-Based FPGAs.	298
v1.3 (October 2008)	The "UJTAG Support in Flash-Based Devices" section was revised to include new families and make the information more concise.	298
	The title of Table 16-3 • Configuration Bits of Fusion, IGLOO, and ProASIC3 CCC Blocks was revised to include Fusion.	302
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 16-1 • Flash-Based FPGAs: <ul style="list-style-type: none"> ProASIC3L was updated to include 1.5 V. The number of PLLs for ProASIC3E was changed from five to six. 	298
v1.1 (March 2008)	The chapter was updated to include the IGLOO PLUS family and information regarding 15 k gate devices.	N/A
	The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	298

Index

Numerics

5 V input and output tolerance 171

A

AES encryption 239

architecture 131

four I/O banks 13

global 31

IGLOO 12

IGLOO nano 11

IGLOO PLUS 13

IGLOOe 14

ProASIC3 nano 11

ProASIC3E 14

routing 18

spine 41

SRAM and FIFO 135

architecture overview 11

array coordinates 16

B

boundary scan 291

board-level recommendations 294

chain 293

opcodes 293

brownout voltage 315

C

CCC 82

board-level considerations 112

cascading 109

Fusion locations 83

global resources 62

hardwired I/O clock input 108

IGLOO locations 81

IGLOOe locations 82

locations 80

naming conventions 179

overview 61

ProASIC3 locations 81

ProASIC3E locations 82

programming 62

software configuration 96

with integrated PLLs 79

without integrated PLLs 79

chip global aggregation 43

CLKDLY macro 65

clock aggregation 44

clock macros 46

clock sources

core logic 76

PLL and CLKDLY macros 73

clocks

delay adjustment 86

detailed usage information 104

multipliers and dividers 85

phase adjustment 87

physical constraints for quadrant clocks 108

SmartGen settings 105

static timing analysis 107

cold-sparing 170, 316

compiling 195

report 195

contacting Microsemi SoC Products Group

customer service 321

email 321

web-based technical support 321

customer service 321

D

DDR

architecture 205

design example 216

I/O options 207

input/output support 209

instantiating registers 210

design example 55

design recommendations 46

device architecture 131

DirectC 280

DirectC code 285

dual-tile designs 160

E

efficient long-line resources 19

encryption 289

ESD protection 171

F

FIFO

features 141

initializing 148

memory block consumption 147

software support 154

usage 144

flash switch for programming 9

FlashLock

IGLOO and ProASIC devices 241

permanent 241

FlashROM

access using JTAG port 123

architecture 267

- email 321
- My Cases 322
- outside the U.S. 322
- technical support 321
- website 321
- programmers 225
 - device support 228
- programming
 - AES encryption 253
 - basics 223
 - features 223
 - file header definition 257
 - flash and antifuse 225
 - flash devices 223
 - glossary 258
 - guidelines for flash programming 229
 - header pin numbers 270
 - microprocessor 283
 - power supplies 263
 - security 247
 - solution 268
 - solutions 227
 - voltage 263
 - volume services 226
- programming support 221

R

RAM

- memory block consumption 147
- remote upgrade via TCP/IP 288
- routing structure 18

S

- Schmitt trigger 174
- security 264
 - architecture 237
 - encrypted programming 288
 - examples 242
 - features 238
 - FlashLock 241
 - FlashROM 121
 - FlashROM use models 245
 - in programmable logic 235
 - overview 235
- signal integrity problem 271
- silicon testing 304
- single tile designs 159
- SmartGen 154
- spine architecture 41

- spine assignment 52
- SRAM
 - features 137
 - initializing 148
 - software support 154
 - usage 141
- SSOs 176
- STAPL player 285
- STAPL vs. DirectC 287
- switching circuit 278
 - verification 278
- synthesizing 192

T

- TAP controller state machine 291, 300
- tech support
 - ITAR 322
 - My Cases 322
 - outside the U.S. 322
- technical support 321
- transient current
 - VCC 310
 - VCCI 310
- transient current, power-up/-down 309

U

- UJTAG
 - CCC dynamic reconfiguration 302
 - fine tuning 303
 - macro 299
 - operation 300
 - port usage 301
 - use to read FlashROM contents 297
- ultra-fast local lines 18

V

- variable aspect ratio and cascading 145
- VersaNet global networks 33
- VersaTile 15
- very-long-line resources 19
- ViewDraw 191
- VREF pins
 - manually assigning 199

W

- weak pull-down 175
- weak pull-up 175
- web-based technical support 321